SHANGHAI SUNRISE ELECTRONICS CO., LTD.

XR-85

SILICON EPITAXIAL
PLANAR SWITCHING DIODE

REVERSE VOLTAGE: 20V
FORWARD CURRENT: 100mA

TECHNICAL SPECIFICATION

FEATURES

- Small glass structure ensures high reliability
- Low leakage
- High temperature soldering guaranteed: 250°C/10S/9.5mm lead length at 5 lbs tension

MECHANICAL DATA

- Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C
- Case: Glass,hermetically sealed
- Polarity: Color band denotes cathode
- Mounting position: Any

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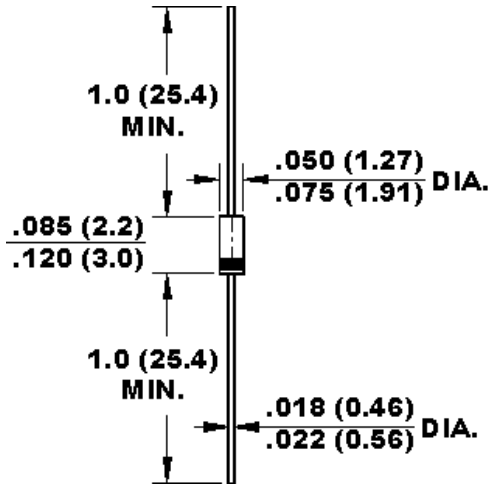

Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified)

RATINGS	SYMBOL	VALUE	UNITS
Reverse Voltage	V_R	20	V
Peak Reverse Voltage	V_{RM}	35	V
Forward Current (average)	I_O	100	mA
Forward Voltage (I_F=10mA)	V_F	1	V
Reverse Current (V_R=20V)	I_{R1}	100	nA
Reverse Current (V_R=20V,T_J=100°C)	I_{R2}	10	μA
Capacitance (Note 1)	C_t	1.5	pF
Forward Differential Resistor (I_F=10mA, f=100MHz)	r_F	0.6	Ω
Thermal Resistance (junction to ambient) (Note 2)	R_θ(ja)	0.35	°C/mW
Operating Junction and Storage Temperature Range	T_{STG},T_J	-55 ~ +150	°C

Notes:

1: V_R=10V, f=1 MHz

2: Valid provided that leads are kept at ambient temperature at a distance of 8mm from case.